

5A Step-Down Converter with I²C Interface

General Description

The RT5735A device is a full featured 5.5V, 5A, synchronous step down constant-on-time (COT) current mode converter with two integrated MOSFETs. The RT5735A enables small designs by integrating the MOSFETs, implementing current mode control to reduce external component count, reducing inductor size by enabling up to 2.4MHz switching frequency, and minimizing the IC footprint with a small WL-CSP-20B 1.6x2 (BSC) package. The RT5735A provides accurate regulation for a variety of loads with an accurate ±1% Voltage Reference (VREF) over temperature. Efficiency is maximized through the integrated $34m\Omega/18m\Omega$ MOSFETs and 70μ A typical quiescent current. Using the enable pin, shutdown supply current is less than 2µA by entering a shutdown mode.

The output voltage startup ramp is controlled by the slow start pin. An open-drain power good signal indicates the output is within 90% to 95% of its nominal voltage.

Marking Information



4A : Product Code W : Date Code

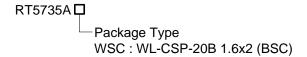
Features

- 2.5V to 5.5V Input Supply Voltage
- Current Mode COT Control Loop Design
- Fast Transient Response
- Internal $34m\Omega$ and $18m\Omega$ Synchronous Rectifier
- Highly Accurate V_{OUT} Regulation Over Load/Line Range
- Robust Loop Stability with Low-ESR Cout
- Over-Temperature Protection

Applications

- Distributed Power Systems
- Enterprise Servers, Ethernet Switches & Routers, and Global Storage Equipment
- Telecom & Industrial Equipment

Ordering Information

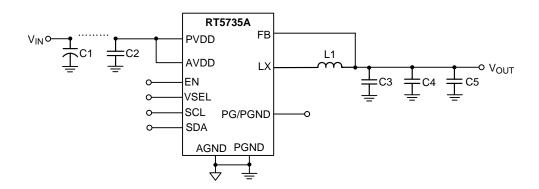


Note:

Richtek products are:

- ▶ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- ▶ Suitable for use in SnPb or Pb-free soldering processes.

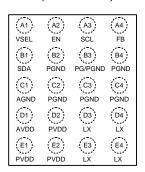
Simplified Application Circuit





Pin Configurations

(TOP VIEW)



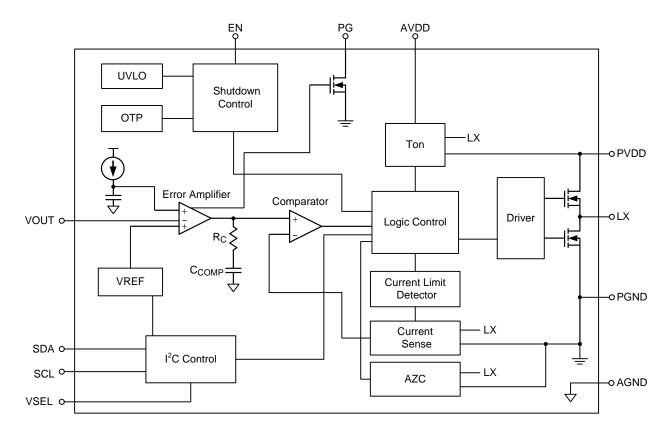
WL-CSP-20B 1.6x2 (BSC)

Functional Pin Description

Pin No.	Pin Name	Pin Function
A1	VSEL	Output Voltage/ Mode Selection. The level determines which of two programmable, configurations to utilize (operating mode / output voltage). There is an internal pull down resistor on this pin; could be left open if not used.
A2	EN	Enable Control Input. Active high will enable the part. There is an internal pull-down resistor on this pin.
А3	SCL	I ² C Clock Input.
A4	FB	Output Voltage Pin.
B1	SDA	I ² C Data Input.
В3	PG/PGND	Power Good Open-Drain Output. If not used, it has to be connected to ground plane.
B2, B4, C2, C3, C4	PGND	Power Ground.
C1	AGND	Analog Ground should be electrically connected to GND close to the device.
D1	AVDD	Analog Circuit Input Supply Voltage.
D2, E1, E2	PVDD	Input Supply Voltage, 2.5V to 5.5V.
D3, D4, E3, E4	LX	Switch Node. The source of the internal high-side power MOSFET, and drain of the internal low-side (synchronous) rectifier MOSFET.



Function Block Diagram



Operation

The RT5735A is a synchronous low voltage step-down converter that can support the input voltage range from 2.5V to 5.5Vand the output current can be up to 5A. The RT5735A uses a constant on-time, current mode architecture. In steady-state operation, the high-side N-MOSFET is turned on when the current feedback reaches COMP level which is the amplified difference between the reference voltage and the feedback voltage. The on time of high-side N-MOSFET is determined by on-time generator which is a function of input and output voltage. After on-time expires, high-side MOSFET is turned off and low-side MOSFET is turned on. Until the low-side current sensing signal reaches the COMP, the high-side MOSFET is turned on again. In this manner, the converter regulates the output voltage and keeps the frequency constant.

The switching frequency is 2.4MHz allows for efficiency and size optimization when selecting the output filter components.

The RT5735A reduces the external component count by integrating the boot recharge MOSFET.

The error amplifier EA adjusts COMP voltage by comparing the output voltage with the internal I^2C set reference voltage. When the load increases, it causes a drop in the output voltage relative to the reference, then the COMP voltage rises to allow higher inductor current to match the load current.

PWM Frequency and Adaptive On Time Control

The on-time can be roughly estimated by the equation:

$$T_{on} = \frac{V_{OUT}}{V_{IN}} \times \frac{1}{F_{SW}}$$
 where F_{SW} is nominal 2.4MHz



Auto-Zero Current Detector

The auto-zero current detector circuit senses the LX waveform to adjust the zero current threshold voltage. When the current of low-side MOSFET decreases to the zero current threshold, the low-side MOSFET turns off to prevent negative inductor current. In this way, the zero current threshold can adjust for different condition to get better efficiency.

Protection Features

The RT5735A has many features to protect the device.

Under-Voltage Protection (UVLO)

The UVLO continuously monitors the voltage of AVDD to make sure the device works properly. When the AVDD is high enough to reach the high threshold voltage of UVLO, the step-down converter softly starts or pre-bias to its regulated output voltage. When the AVDD decreases to its low threshold (180mV hysteresis), the device will shut down.

Power Good

When the output voltage is higher than PG rising threshold, the PG flag is High.

Output Under-Voltage Protection (UVP)

When the output voltage is lower than 400mV after soft-start end is ok, the UVP is triggered. When UVP occurs, the device enters hiccup mode.

Over-Current Protection (OCP)

The RT5735A senses the current signal when low-side MOSFET turns on and uses a valley current limiting circuit. As a result, the OCP set point is the OCP DC limit minus half of the ripple current. The OCP is cycle-by-cycle limit. If the OCP occurs, the converter holds off the next on pulse until inductor current drops below the OCP limit. If the OCP keeps and the load current is larger than the current provided by the converter, the output voltage drops. When the output voltage triggers UVP, the converter enters hiccup mode.

Soft-Start

An internal current source charges an internal capacitor to build the soft-start ramp voltage. The typical soft-start time is $130\mu s$.

Over-Temperature Protection (OTP)

The RT5735A has over-temperature protection. When the device triggers the OTP, the device shuts down.



Absolute Maximum Ratings (Note 1)

Su	oply Input Voltage,	V _{IN}	–0.3V to 6V
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• Power Dissipation, P_D @ $T_A = 25^{\circ}C$

WL-CSP-20B 1.6x2 (BSC) ------ 1.818W

• Package Thermal Resistance (Note 2)

WL-CSP-20B 1.6x2 (BSC), θ_{JA} ------ 55°C/W

WL-CSP-20B 1.6x2 (BSC), θ_{JC}------7°C/W

• Lead Temperature (Soldering, 10 sec.)------ 260°C

• Junction Temperature ------ 150°C

• ESD Susceptibility (Note 3)

HBM (Human Body Model) ----- 2kV

Recommended Operating Conditions (Note 4)

• Supply Input Voltage ----- 2.5V to 5.5V

Electrical Characteristics

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 $(V_{IN} = 3.6V, T_A = 25^{\circ}C, unless otherwise specified)$

Para	ameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Supply Curre	ent						
Operating Qui	escent Current	I _{Q_PWM}	PWM Mode IQ at I _{OUT} = 0A (Note 5)		10	20	mA
Operating Qui	escent Current	I _{Q_PFM}	PSM Mode IQ at I _{OUT} = 0A		70		μА
Product in Off	Mode	I _{OFF}	EN, VSEL Low, $V_{IN} = 2.5V$ to 5.5V		1	5	μΑ
DC/DC Conve	erter						
Operation Inp	ut Voltage	VIN		2.5		5.5	V
Output Valtage	o DC Error	A	PWM Mode	-1		1	%
Output Voltage	e DC Elloi	Δ VOUT	PSM Mode	-1		2	70
Switching Free	quency	F _{SW}		2.16	2.4	2.64	MHz
Day	High-Side	R _{ON_H}	V _{IN} = 5V		34		mO
R _{ON}	Low-Side	Ron_L	V _{IN} = 5V		18		mΩ
			I _{OC} = 00 Valley Current (Note 5)		4		
Valloy Current	Valley Current Limit Level		I _{OC} = 01 Valley Current (Note 5)		4.7		A
valley Current			I _{OC} = 10 Valley Current (Note 5)	= 10 Valley Current (Note 5) 5.4			
			Ioc = 11 Valley Current	5.4	6.4	7.4	



Parai	meter	Symbol	Test Conditions	Min	Тур	Max	Unit
Load Regulation	n	ΔV_{LOAD}	lout from 300mA to loutMAX (Note 5)		0.2		%/A
Line Regulation	າ	ΔV_{LINE}	$2.5V \le V_{IN} \le 5.5V$		0.3		%
Transient Load	Response	AC _{LOAD}	$tr = ts = 0.1 \mu s$ Load Step 0 to 1.2A (Note 5)		±40		mV
Turn On Time		т	Time from EN Transition from Low to High to 90% of Output Voltage		70		0
Tum On Time		T _{start}	Time from EN Transition from Low to High to Vout		130		μS
DC/DC Active ODischarge	Output	Rdischg	Force Vout = 1.15V, EN = Low		16		Ω
EN. VSEL							
Input Voltage	Logic-High	V _{IH}		1.05	-		V
input voitage	Logic-Low	VIL				0.4	V
PG							
Power Good H	igh Hysteresis	VPGH	Rising Edge as a Percentage of Nominal Output Voltage	90	94	98	%
Power Good Lo	ow Threshold	V _{PGL}	Falling Edge as a Percentage of Nominal Output Voltage	86	90	94	%
Power Good R	eaction Time	T _{RT}	Falling		3.5		
for DC/DC		TRI	Rising	3.5		14	μS
Power Good Lo Voltage	ow Output	VPGL	Ipg = 5mA			0.2	V
Power Good Le	eakage Current	PG _{LK}	3.6V at PG Pin when Power Good Valid	1	1	100	nA
Power Good H Voltage	igh Output	V _{PGH}	Open-Drain	ı		5.5	V
I ² C							
High Level at S	CL/SDA Line	V ₁₂ CINT		1.7		5	V
SCL, SDA	Logic-High	V ₁₂ CIH		1.7			.,
Input Voltage	Logic-Low	V _{12CIL}				0.5	V
SDA Low Outp	ut Voltage	V _{12COL}	I _{SINK} = 3mA			0.4	V
I ² C Clock Freq	uency	FscL	(Note 5)			3.4	MHz
Total Device							
Under-Voltage Threshold	Lockout	V _{UVLO}	V _{IN} Falling		2.15	2.34	V
V _{IN} POR		V _{POR}	V _{IN} Rising		2.3	2.3 2.45	
Thermal Shutd	own Protection	T _{SD}	(Note 5)		150		°C
Warning Rising Edge		TWARNING	(Note 5)		135		°C
Pre-Warning TI	hreshold	T _{PWTH}	For Default Setting (Note 5)		105		°C
Thermal Shutd	own Hysteresis	T _{SDH}	(Note 5)		30		°C
Thermal Warni	ng Hysteresis	Twarning_hys	(Note 5)		15		°C
	•				_	_	_

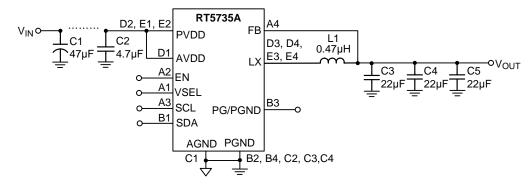
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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Thermal Pre-Warning Hysteresis	T _{PWTH_HYS}	(Note 5)		6		°C

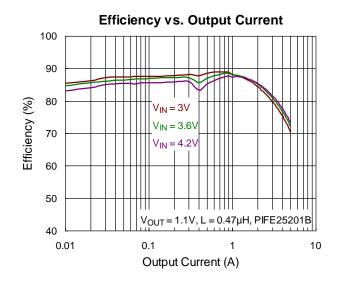
- **Note 1.** Stresses beyond those listed "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.
- Note 2. θ_{JA} is measured at $T_A = 25^{\circ}C$ on a high effective thermal conductivity four-layer test board per JEDEC 51-7. θ_{JC} is measured at the exposed pad of the package.
- Note 3. Devices are ESD sensitive. Handling precaution recommended.
- **Note 4.** The device is not guaranteed to function outside its operating conditions.
- Note 5. Guaranteed by design and characterized.

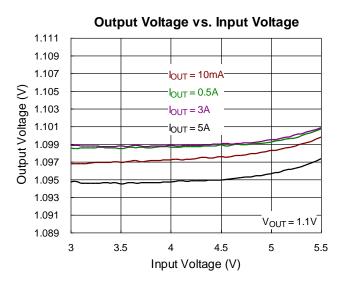
Typical Application Circuit

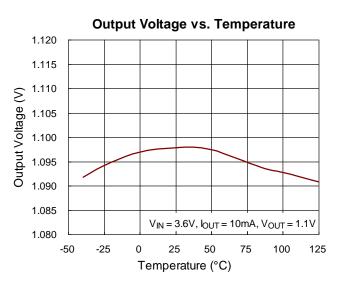


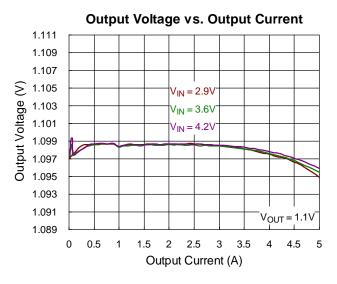


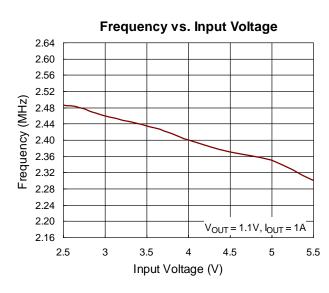
Typical Operating Characteristics

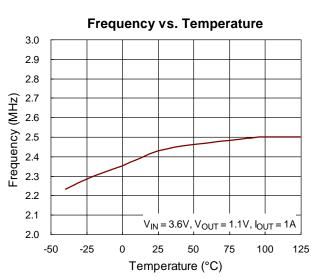




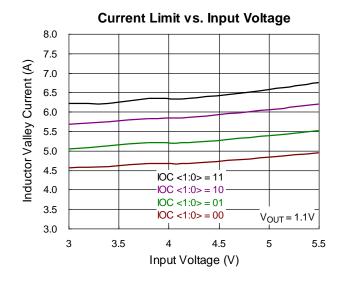


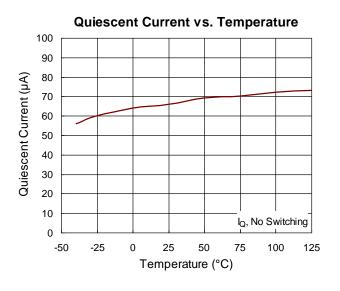


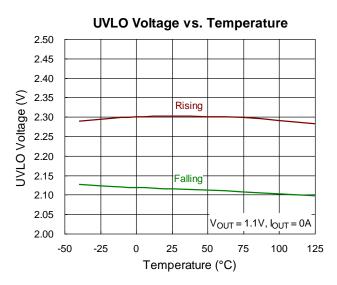


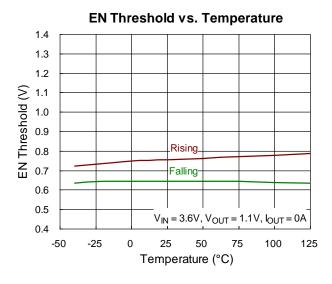


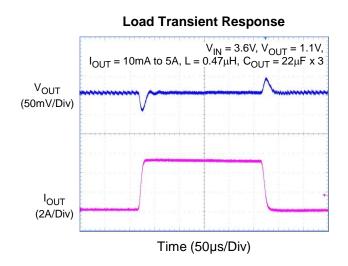


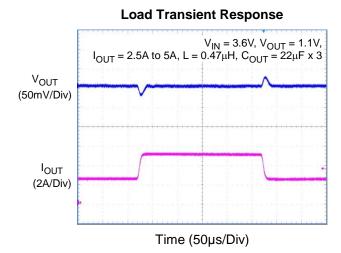




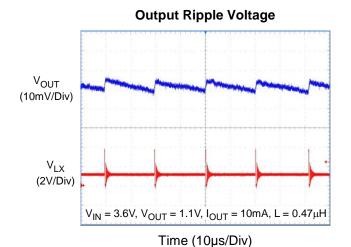


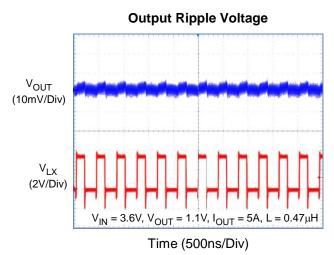


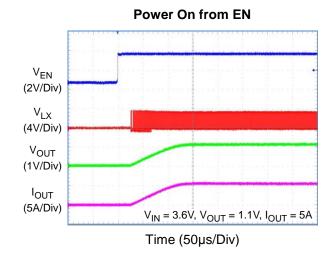


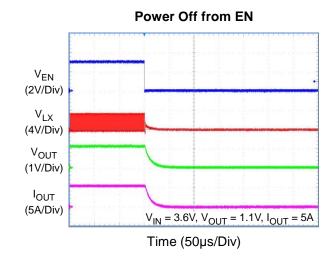














Application Information

The basic RT5735A application circuit is shown in Typical Application Circuit. External component selection is determined by the maximum load current and begins with the selection of the inductor value and operating frequency followed by C_{IN} and C_{OUT}.

Inductor Selection

The inductor value and operating frequency determine the ripple current according to a specific input and output voltage. The ripple current, ΔI_L , increases with higher V_{IN} and decreases with higher inductance, as shown in equation below :

$$\Delta I_L = \left[\frac{V_{OUT}}{f \times L}\right] \times \left[1 - \frac{V_{OUT}}{V_{IN}}\right]$$

where f is the operating frequency and L is the inductance. Having a lower ripple current reduces not only the ESR losses in the output capacitors, but also the output voltage ripple. Higher operating frequency combined with smaller ripple current is necessary to achieve high efficiency. Thus, a large inductor is required to attain this goal. The largest ripple current occurs at the highest V_{IN}. A reasonable starting point for selecting the ripple current is $\Delta I_L = 0.3 \times I_{MAX}$ to $0.4 \times I_{MAX}$. To guarantee that the ripple current stays below a specified maximum, the inductor value should be chosen according to the following equation :

$$L = \left[\frac{V_{OUT}}{f \times \Delta I_{L(MAX)}} \right] \times \left[1 - \frac{V_{OUT}}{V_{IN(MAX)}} \right]$$

The inductor's current rating (defined by a temperature rise from 25°C ambient to 40°C) should be greater than the maximum load current and its saturation current should be greater than the short-circuit peak current limit.

Input and Output Capacitor Selection

An input capacitor, C_{IN} , is needed to filter out the trapezoidal current at the source of the high-side MOSFET. To prevent large ripple current, a low ESR input capacitor sized for the maximum RMS current should be used. The RMS current is given by :

$$I_{RMS} = I_{OUT(MAX)} \frac{V_{OUT}}{V_{IN}} \sqrt{\frac{V_{IN}}{V_{OUT}} - 1}$$

This formula has a maximum at $V_{IN} = 2V_{OUT}$, where $I_{RMS} = I_{OUT(MAX)} / 2$. This simple worst-case condition is commonly used for design. Choose a capacitor rated at a higher temperature than required. Several capacitors may also be paralleled to meet the size or height requirements of the design. Ceramic capacitors have high ripple current, high voltage rating and low ESR, which makes them ideal for switching regulator applications. However, they can also have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can lead to significant ringing. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input, V_{IN}. At best, this ringing can couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at V_{IN} large enough to damage the part. Thus, care must be taken to select a suitable input capacitor.

The selection of C_{OUT} is determined by the required ESR to minimize output voltage ripple. Moreover, the amount of bulk capacitance is also a key for C_{OUT} selection to ensure that the control loop is stable. Loop stability can be checked by viewing the load transient response. The output voltage ripple, ΔV_{OUT} , is determined by :

$$\Delta V_{OUT} \leq \Delta I_L \Bigg[\text{ESR} + \frac{1}{8 f_{OSC} \ C_{OUT}} \Bigg]$$

where fosc is the switching frequency and ΔI_L is the inductor ripple current. The output voltage ripple will be the highest at the maximum input voltage since ΔI_L increases with input voltage. Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirement. Ceramic capacitors have excellent low ESR characteristics, but can have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can also lead to significant ringing. Nevertheless, high value, low cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications.

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I²C Interface Function

RT5735A can be used by I²C interface to select Vout voltage level, over current limit level, thermal warning temperature level, PWM control mode, and so on. The register of each function can be found from the following register map and it also explains how to use these function.

Vout Selection: RT5735A has external VSEL pin to select PROGVSEL1(0X10) or PROGVSEL0(0X11) which can control Vout from 0.6V to 1393.75mV with 7bits resolution. Pull VSEL to high is for PROGVSEL1 and pull VSEL to low is for PROGVSEL0. If VSELGT bit in the COMMAND register is set to 0, Vout will only be controlled by PROGVSEL1.

Discharge Function: In the PGOOD register DISCHG bit is set to 1 can let V_{OUT} discharge by internal resistor when converter shuts down. If setting to 0 V_{OUT} will decrease depending on the loading.

Power Good Function : In the PGOOD register PGDCDC bit can control if external PG pin is active. After PG function is active if PGDVS pin is 0, PG will not change state during V_{OUT} changing. Once PGDVS pin is 1 PG will be low when V_{OUT} is much lower than V_{REF} during V_{OUT} changing.

Slew Rate Setting: RT5735A can control slew rate as VouT changing between two voltage levels for both up and down. In the time register DVS_UP bits can control up-speed when in the LIMCONF register DVS_DOWN can control down-speed. DVS_DOWN is valid only when converter is at PWM mode or DVSMODE bit is 1.

Force PWM Mode: In the COMMAND register PWMSEL0 and PWMSEL1 can decide converter is always at PWM mode or enters power saving mode at light load condition. During output voltage is changed from high to low at light load, setting DVSMODE bit to 1 will make transition operate at PWM mode and output voltage will decrease quickly. If setting to 0, the output voltage will decrease depending on the loading.

Over Current Level : RT5735A has four levels of over current limit to be selected. Using IOC bits in the LIMCONF register can change different inductor valley current limit level.

Thermal Shutdown Protection: The default REARM bit in the LIMCONF register is 1. RT5735A will shut down switching operation when the junction temperature exceeds 150 °C. Once the junction temperature cools down by approximately 30°C the IC will resume normal operation with a complete soft-start. When REARM bit is set to 0, once the device triggers the OTP, the system will be latched and the output voltage will no longer be regulated during OTP latched state. Re-start input voltage or EN pin can unlatch the protection state. Using I²C to shutdown the system and then re-enable it will also unlatch UVP function.



The RT5735A default I^2C slave address = 7'b0011100. I^2C interface support fast mode (bit rate up to 400kb/s). The write or read bit stream (N≥1) is shown below :

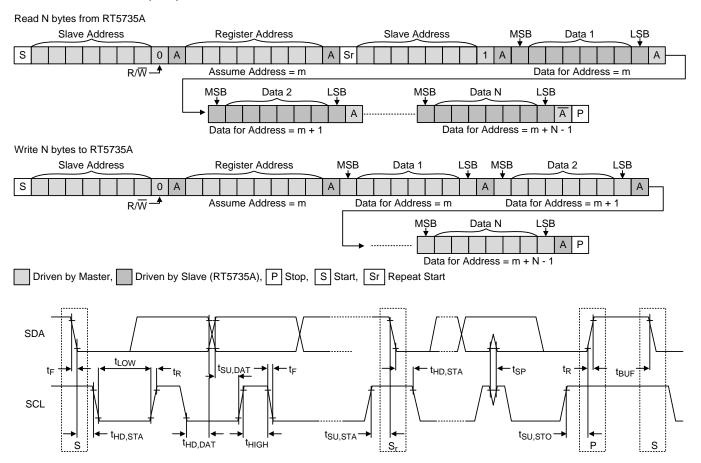


Figure 1. I²C Read and Write Stream and Timing Diagram

RT5735A can also support High-speed mode(bit rate up to 3.4Mb/s) with access code 08H. Figure 2 and Figure 3 show detail transfer format. Hs-mode can only commence after the following conditions (all of which are in F/S-mode):

- ► START condition (S)
- ▶ 8-bit master code (00001xxx)
- ▶ not-acknowledge bit (Ā)

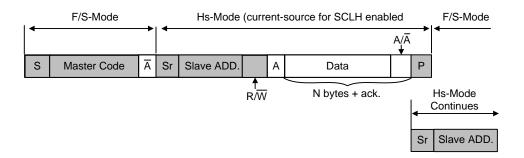


Figure 2. Data Transfer Format in Hs-mode

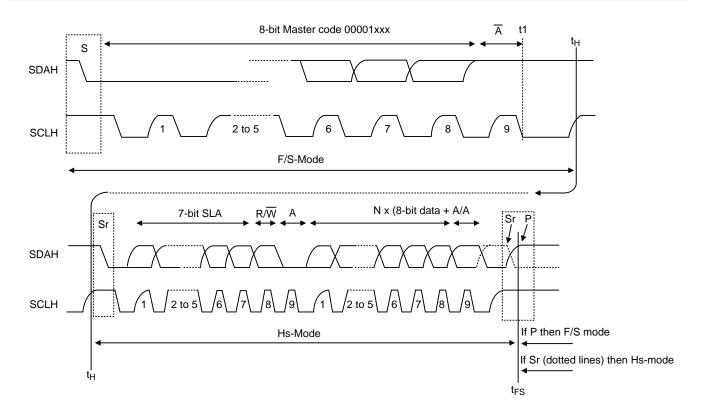


Figure 3. A Complete Hs-mode Transfer



Address Name		egister ddress	Bit7	Bit6	Bit5	Bit4	Bit3	Bit2	Bit1	Bit0	
		Meaning			1	PRODU	JCT_ID		1		
PRODUCT _ID	0x03	Default	0	0	0	1	0	0	0	0	
_10		Read/Write	R	R	R	R	R	R	R	R	
		Meaning				REVISI	ON_ID				
REVISION _ID	0x04	Default	0	0	0	0	0	0	0	0	
_10		Read/Write	R	R	R	R	R	R	R	R	
		Meaning				FEATU	RE_ID				
FEATURE _ID	0x05	Default	0	0	0	0	0	0	0	0	
_10		Read/Write	R	R	R	R	R	R	R	R	
		Meaning				VENDI	ER_ID				
VENDER ID	0x06	Default	1	0	0	0	1	0	0	0	
		Read/Write	R	R	R	R	R	R	R	R	
		Meaning	ENVSEL1			Vo	ut_VSEL	1[6:0]			
PROGVSEL1	0x10	Default	0	1	0	1	0	0	0	0	
		Read/Write	RW	RW	RW	RW	RW	RW	RW	RW	
		Meaning	ENVSEL0 Vout_VSEL0[6:0]								
PROGVSEL0	0x11	Default	0	0	0	1	0	0	0	0	
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W	
		Meaning		RESV		DISCHG		RESV	PGDVS	PGDCDC	
PGOOD	0x12	Default	0	0	0	0	0	0	0	0	
		Read/Write	R	R	R	R/W	R	R	R/W	R/W	
		Meaning		RESV			DVS_UF	P[2:0]	RES	SV	
TIME	0x13	Default	0	0	0	1	1	0	0	1	
		Read/Write	R	R	R	R/W	R/W	R/W	R	R	
		Meaning	PWMSEL0	PWMSEL1	DVSMODE			RESV		VSELGT	
COMMAND	0x14	Default	0	0	0	0	0	0	0	1	
		Read/Write	R/W	R/W	R/W	R	R	R	R	R/W	
		Meaning	100	C<1:0>	TPWTH<1	:0>	RESV	DVS_DO	WN<1:0>	REARM	
LIMCONF	0x16	Default	0	1	1	0	0	0	1	1	
		Read/Write	R/W	R/W	R/W	R/W	R	R/W	R/W	R/W	



Register Name		legister lddress	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
		Meaning				PRODU	JCT_ID			
PRODUCT _ID	0X03	Default	0	0	0	1	0	0	0	0
		_ID -	Read/Write	R	R	R	R	R	R	R
PRO	PRODUCT_ID			T_ID						

Register Name		legister Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
		Meaning		REVISION_ID						
REVISION _ID		Default	0	0	0	0	0	0	0	0
		Read/Write	R	R	R	R	R	R	R	R
REV	REVISION_ID			N_ID						

Register Name		legister Address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
		Meaning				FEATU	JRE_ID			
FEATURE_ ID		Default	0	0	0	0	0	0	0	0
		 	Read/Write R R R	R	R	R	R	R		
FEA	FEATURE_ID			E_ID						

Register Name		legister address	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)	
	0X06	Meaning				RE	SV				
VENDER ID		ER 0x06 [Default	1	0	0	0	1	0	0	0
			Read/Write	R	R	R	R	R	R	R	R
VEI	VENDER ID			ID							

Register Name	Name Address		b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)
		Meaning	ENVSEL1			Vou	ut_VSEL1[6:0]		
PROGVSE L1	0x10	Default	0	1	0	1	0	0	0	0
		Read/Write	RW	RW	RW	RW	RW	RW	RW	RW
EN	IVSE	L1	EN Pin Gating for VSEL internal signal = High 0 : Disabled 1 : Enabled							
Vout_	VSEL	.1[6:0]	SEL[6:0] = SEL[6:0] =	: 1111111 : 1010000: : 0000000	VOUT = 1 :0.6V	1393.75mV .1V (defaul = 600mV +	t)	SEL		



Register Name	Name Address		b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)		
		Meaning	ENVSEL0	ENVSEL0 Vout_VSEL0[6:0]								
PROGVSE L0	0x11	Default	0	0	0	1	0	0	0	0		
		Read/Write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W		
EN Pin Gating for VSEL internation of the control o						ıl signal= L	OW					
1 : Enabled VID Table satisfy : SEL[6:0] = 11111111 : VOUT = 1393.75mV Vout_VSEL0[6:0] = 0010000 : VOUT = 0.7V (default) SEL[6:0] = 00000000 : 0.6V 6.25mV step for DCDC, VOUT = 600mV + 6.25mV x SEL												

Register Name			b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)			
		Meaning	RESV			DISCHG	RE	SV	PGDVS	PGDCDC			
PGOOD	0x12	Default	0	0	0	0	0	0	0	0			
		Read/Write	R	R	R	R/W	R	R	R/W	R/W			
	RESV			Reserved bits									
DISCHG			Active discharge bit enabling 0 : Discharge path disabled 1 : Discharge path enabled										
	RESV	,	Reserved bits										
PGDVS			Power good active on DVS 0 : Disabled 1 : Enabled										
PGDCDC			Power good enabling 0 : Disabled 1 : Enabled										

Register Name		egister ddress	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)	
		Meaning	Reserved			DVS_UP[2:0]			Reserved		
TIME	0x13	Default	0	0	0	1	1	0	0	1	
		Read/Write	R	R	R	R/W	R/W	R/W	R	R	
	RESV			bits							
DVS_UP[2:0]		DVS slev 000 : 64n 001 : 16n 010 : 32n 011 : 8m 100 : 4m 101 : 4m 110 : 32n 111 : 8m	nV/μS nV/μS V/μS V/μS V/μS nV/μS)							
	RESV			Reserved bits							



Register Name		egister ddress	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)	
		Meaning	PWMSEL0	PWMSEL1		VSELGT					
COMMAN	0x14	Default	0	0	0	0	0	0	0	1	
		Read/Write R/W	R/W	R/W	R	R	R	R	R/W		
PV	PWMSEL0			Operation mode for VSEL internal signal = Low 0 : Auto 1 : Forced PWM							
PWMSEL1			Operation mode for VSEL internal signal = High 0 : Auto 1 : Forced PWM								
DVSMODE			DVS transition mode selection 0 : Auto 1 : Forced PWM								
RESV			Reserved bits								
VSELGT		VSEL Pin gating 0 : Disabled 1 : Enabled									

Register Name		egister ddress	b[7] (MSB)	b[6]	b[5]	b[4]	b[3]	b[2]	b[1]	b[0] (LSB)	
		Meaning	IOC<1:0>		TPWT	H<1:0>	RESV	DVS_DOWN<1:0>		REARM	
LIMCONF	0x16	Default	0	1	1	0	0	0	1	1	
		Read/Write	R/W	R/W	R/W	R/W	R	R/W	R/W	R/W	
IOC[1:0]			Inductor valley current settings 00 = 4A (typ.) 01 = 4.7A (typ.) 10 = 5.4A (typ.) 11 = 6.4A (typ.)								
TPWTH[1:0]			Thermal pre-warning threshold settings $00 = 83^{\circ}C$ $01 = 94^{\circ}C$ $10 = 105^{\circ}C$ $11 = 116^{\circ}C$								
	RESV	1	Reserved bits								
DVS_DOWN[1:0]		DVS slew rate for down 00 = 32mV/μs 01 = 4mV/μs 10 = 8mV/μs 11 = 16mV/μs									
REARM			0 : No Re	of device a ecovery after ery after T	r TSD	_					



Thermal Considerations

For continuous operation, do not exceed absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated by the following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_{A}) / \theta_{JA}$$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction to ambient thermal resistance.

For recommended operating condition specifications, the maximum junction temperature is 125°C. The junction to ambient thermal resistance, θ_{JA} , is layout dependent. For WL-CSP-20B 1.6x2 (BSC) package, the thermal resistance, θ_{JA} , is 55°C/W on a standard JEDEC 51-7 four-layer thermal test board. The maximum power dissipation at $T_A=25^\circ\text{C}$ can be calculated by the following formula :

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C) / (55^{\circ}C/W) = 1.8W$ for WL-CSP-20B 1.6x2 (BSC) package

The maximum power dissipation depends on the operating ambient temperature for fixed $T_{J(MAX)}$ and thermal resistance, θ_{JA} . The derating curve in Figure 4 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

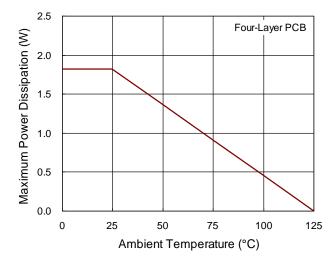


Figure 4. Derating Curve of Maximum Power
Dissipation

Layout Considerations

For best performance of the RT5735A, the following layout guidelines must be strictly followed.

- Input capacitor must be placed as close to the IC as possible.
- ➤ SW should be connected to inductor by wide and short trace. Keep sensitive components away from this trace.
- ► Keep every trace connected to pin as wide as possible for improving thermal dissipation.



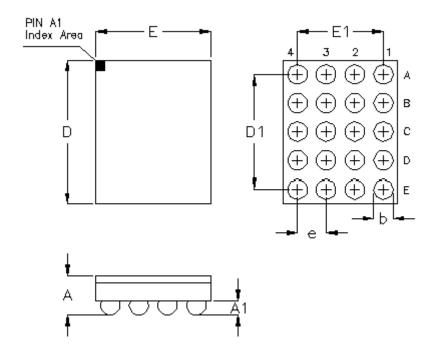
Top layer

AGND and PGND connect Vias can help to reduce power trace and improve together at negative of Cin, thermal dissipation. PGND pins connect top layer Vout connects to FB to reduce noise. and 2nd layer directly for thermal dissipation. pin from 2nd layer. **GND** 9 0 0 1608 Cout 22µF (LX E4 Vout connects to FB pin from 2nd layer VIN **VOUT** Input capacitor must be placed as close SW should be connected to inductor by wide and short to the IC as possible. Suggest layout trace. Keep sensitive components away from this trace. trace wider for thermal dissipation. Suggest layout trace wider for thermal dissipation .

Figure 5. PCB Layout Guide



Outline Dimension



Symbol	Dimensions	In Millimeters	Dimensions In Inches			
Symbol	Min. Max.		Min.	Max.		
А	0.500	0.600	0.020	0.024		
A1	0.170	0.230	0.007	0.009		
b	0.240	0.300	0.009	0.012		
D	1.950	2.050	0.077	0.081		
D1	1.600		0.0	063		
E	1.550	1.650	0.061	0.065		
E1	1.200		0.047			
е	0.4	100	0.016			

20B WL-CSP 1.6x2 Package (BSC)

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